## Strong dependence of the interlayer coupling on the hole mobility in antiferromagnetic $La_{2-x}Sr_xCuO_4$ (x < 0.02)

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We have studied the magnetic coupling between the  $CuO_2$  planes in the antiferromagnetic (AF) phase of Srand Zn-doped La<sub>2</sub>CuO<sub>4</sub> by analyzing the spin-flip transition in the magnetization curves. We find that the interlayer coupling plays a key role in the suppression of the AF phase, and that only mobile holes cause a strong frustration of the interlayer coupling. Depending on the hole mobility, samples with identical Néel temperature can have a very different interlayer coupling.

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All cuprate high-temperature superconductors are characterized by a layered crystal structure. Key elements of this structure are the CuO<sub>2</sub> planes which are a prototype of a spin S=1/2 two-dimensional (2D) Heisenberg antiferromagnet. Insulating CuO<sub>2</sub> planes, such as those in undoped La<sub>2</sub>CuO<sub>4</sub>, exhibit a three-dimensional antiferromagnetic (3D AF) order, while CuO<sub>2</sub> planes doped with hole-like charge carriers, as those in La<sub>2-x</sub>Sr<sub>x</sub>CuO<sub>4</sub>, become superconducting.<sup>1</sup> Both phenomena, antiferromagnetic order as well as superconductivity, depend on a finite electronic coupling between the planes.<sup>2</sup> In this paper we focus on the doping dependence of the interlayer coupling in the AF phase of lightly Sr-doped La<sub>2</sub>CuO<sub>4</sub>.

In La<sub>2-x</sub>Sr<sub>x</sub>CuO<sub>4</sub> the 3D AF order is destroyed by a remarkably small amount of 2% holes (x=0.02), which is in sharp contrast to  $\sim 41\%$  in the case of the substitution of Cu with nonmagnetic Zn.<sup>1,3</sup> Since the suppression of the 3D AF order by holes is a precondition for the occurrence of superconductivity, great efforts have been made to map each stage of this process.<sup>1,4–6</sup> The Néel temperature  $T_N$  decreases from 325 K for x=0 to about 80 K for x=0.019 and then drops to zero at x=0.02<sup>1,6</sup> At the same time for  $x \ge 0.008$  the socalled spin freezing regime evolves at temperatures T $\leq$  30 K.<sup>4,5</sup> At x=0.02 this regime crosses over to the socalled cluster spin-glass phase, which reaches into the superconducting phase that appears at x=0.06<sup>1</sup> Recent neutrondiffraction experiments indicate that the spin freezing regime and the spin-glass phase are closely related.<sup>7</sup> In both phases an incommensurate spin modulation was observed.<sup>7,8</sup> Various models were suggested to describe the suppression of the AF order in  $La_{2-x}Sr_xCuO_4$ .<sup>9-12</sup> The frustration model assumes that individual localized holes cause a frustration of the inplane and the interlayer coupling.<sup>9</sup> In the finite-size scaling model holes segregate into domain walls which limit the 2D correlation length  $\xi_{2D} \propto \sqrt{T_N}$ .<sup>5,10</sup>

To find out the primary controlling parameter for the suppression of the 3D AF order in  $\text{La}_{2-x}\text{Sr}_x\text{CuO}_4$ , we have studied the magnetic interlayer coupling  $J_{\perp}$  as a function of Sr and/or Zn doping. Zn doping is used to reduce the mobility of the holes and to introduce spin vacancies.<sup>6</sup> As  $J_{\perp}$  is about five orders of magnitude weaker than the Cu-O-Cu in-plane superexchange of J=135 meV, it is not possible to measure it by neutron scattering. Instead, we have determined  $J_{\perp}$  from the spin-flip transition which can be induced for  $H \parallel c$  due to the Dzyaloshinsky-Moriya Cu-spin canting.<sup>13</sup> Our analysis of this transition shows that only mobile holes cause a drastic suppression of the interlayer coupling. Codoping with Zn recovers an interlayer coupling nearly as strong as in pure La<sub>2</sub>CuO<sub>4</sub> due to the localization of the holes. Most remarkably, samples with identical hole concentration and similar  $T_N$  can have a very different interlayer coupling, depending on the mobility of the holes.

The dc magnetization M(H) of five polycrystals  $La_{2-x}Sr_xCu_{1-z}Zn_zO_4$  (Table I) was measured with a vibratingsample magnetometer (VSM) with  $T_{max}=290$  K and  $H_{max}=14$  T. Samples were annealed in vacuum (1/2 h, 800 °C), their synthesis is described in Ref. 6.

La<sub>2</sub>CuO<sub>4</sub> exhibits a collinear spin structure with spins nearly parallel to the *b* axis.<sup>13</sup> However, in the lowtemperature orthorhombic (LTO) phase of La<sub>2</sub>CuO<sub>4</sub> the CuO<sub>6</sub> octahedra are tilted, which allows for Dzyaloshinsky– Moriya (DM) superexchange. As a consequence, nearestneighbor Cu spins are slightly canted, which results in small moments  $M_{DM} || c.^{13}$  Below  $T_N$  the DM moments of adjacent planes are AF ordered, but can be ferromagnetically aligned in an external magnetic field  $H || c.^{13}$  The spin flip (SF) takes place when *H* acting on the AF ordered part of the DM moment  $M_{DM}^{AF}$  overcomes the interlayer coupling (left inset

TABLE I. Studied  $La_{2-x}Sr_xCu_{1-z}Zn_zO_4$  samples (see text).

Sr	Zn	<i>Т<sub>N</sub></i> (К)	H <sub>SF</sub> (T)	$M_{DM}^{AF}$ [10 <sup>-3</sup> ( $\mu_{\rm B}/{ m Cu}$ )]	$J_{\perp}$ ( $\mu \mathrm{eV}$ )
0	0	312	4.5(5)	2.7(3)	2.9(5)
0.011	0	222	3.6(3)	2.1(3)	1.7(5)
0.017	0	132	2.4(2)	1.2(2)	0.7(3)
0.017	0.10	134	3.9(4)	3.0(3)	2.7(5)
0	0.15	166	3.6(4)	3.4(3)	2.7(5)



FIG. 1. Magnetization curves M(H) of  $La_{2-x}Sr_xCuO_4$  with x = 0 and x = 0.017 at reduced temperatures  $T/T_N = 1.05$ , 0.9, and 0.2 (see text). In the left panel only data for x = 0.017 is shown since  $1.05 \times T_N$  for x = 0 is above the maximum temperature of our VSM (290 K).

Fig. 2). Once  $M_{DM}^{AF}(T)$  and the spin-flip field  $H_{SF}(T)$  have been extracted from the M(H) curves, the interlayer coupling  $J_{\perp}$  can be calculated from the low-temperature limit,<sup>13</sup>

$$M_{DM}^{AF}(0)H_{SF}(0) \simeq S^2 J_{\perp}.$$
 (1)

The analysis is complicated by the fact that the DM moments, which are of the order of  $\sim 10^{-3} \mu_B/\text{Cu}$ , cause the M(H) curves to be nonlinear in the AF phase as well as in the paramagnetic phase.<sup>13,14</sup> As an example we show in Fig. 1, M(H) of La<sub>2</sub>CuO<sub>4</sub> ( $T_N$ =312 K) and La<sub>1.983</sub>Sr<sub>0.017</sub>CuO<sub>4</sub> ( $T_N$ =132 K) as a function of the reduced temperature  $T/T_N$ . In the paramagnetic phase ( $T/T_N > 1$ ) the nonlinear contribution can be described by a term  $M_B$  which contains a Brillouin function for spin S=1/2 (details below). In the AF phase ( $T/T_N < 1$ ) the nonlinear contribution is always a combination of  $M_B$  and a term  $M_{SF}$  which arises from the spin flip

$$M = \begin{cases} \chi_0 H + M_B & (T > T_N) \\ \chi_0 H + M_B + M_{SF} & (T < T_N) \end{cases} ,$$
 (2)

where  $\chi_0 H$  accounts for all linear terms. As one can see in Fig. 1 the spin-flip term  $M_{SF}$  is zero in the paramagnetic phase, finite but small just below  $T_N$ , and dominant at low T (gray shaded area). Furthermore, one can see that in the Sr-doped sample even at very low temperatures  $M_{SF}$  is significantly smaller than in La<sub>2</sub>CuO<sub>4</sub>, while  $M_B$  is larger, which indicates the reduction of the AF order parameter by the doped holes. Clearly visible is also the smaller critical field  $H_{SF}$  for x=0.017.

In a single crystal the spin flip causes a steplike increase of M(H||c) at  $H \simeq H_{SF}$  by  $M_{SF} = M_{DM}^{AF}$ . In a polycrystal the crystallites are oriented randomly. From integration over all directions we obtain the following field dependence of  $M_{SF}$ for  $H \ge H_{SF}$ :



FIG. 2. Spin-flip term  $M_{SF}=M-M_B-\chi_0H$  in La<sub>2</sub>CuO<sub>4</sub> at 30 K. (Dashed/Solid lines) fit according to Eq. (3) without/with Gaussian distribution of  $H_{SF}$ . Left inset: Spin flip takes place when  $H \cos \theta \| c$  exceeds  $H_{SF}$ . Only  $M_{DM}^{AF} \cos \theta \| H$  contributes to  $M_{SF}$ . Right inset: In a polycrystal  $H_{SF} < H_{max}(dM/dH)$ .

$$M_{SF}(H) = \frac{1}{2} M_{DM}^{AF} [1 - (H_{SF}/H)^2].$$
(3)

Obviously, in a polycrystal  $M_{SF}$  converges to  $M_{DM}^{AF}/2$  for  $H \rightarrow \infty$ . A similar geometrical consideration for the paramagnetic phase yields the phenomenological formula for  $M_B$ ,

$$M_B(H) = M_{DM}^{NO} \int_0^{\pi/2} \tanh(kH\sin\phi)\sin^2\phi d\phi, \qquad (4)$$

where  $M_{DM}^{NO}$  is the non-AF-ordered (NO) fraction of  $M_{DM}$  per Cu spin.  $k=M_{DM}^{NO}N/(k_BT+J_{\perp}N^2S^2)$  is a phenomenological expression with  $N=(\xi_{2D}/a)^2$  the number of 2D correlated Cu spins, which provides an estimate for the magnetic correlation length  $\xi_{2D}$ .  $\phi$  is the angle between H and the tilt axis of the CuO<sub>6</sub> octahedra, which is normal to the DM plane (inset Fig. 2). Our analysis has shown that  $M_{DM} \approx M_{DM}^{AF} + M_{DM}^{NO}$ . A neglect of  $M_B$  would lead to inaccurate values for  $M_{DM}^{AF}$ ,  $H_{SF}$ , and  $J_{\perp}$ , in particular when  $M_B \gtrsim M_{SF}$ . In the following we focus on the spin-flip term  $M_{SF}$ .

In Fig. 2 we show  $M_{SF}=M-M_B-\chi_0H$  for La<sub>2</sub>CuO<sub>4</sub> at 30 K, where  $M_B \approx 0$ . For large *H*, Eq. (3) yields a good fit to the data (dashed line). Assuming a Gaussian distribution of  $H_{SF}$  in the polycrystal, integration of Eq. (3) over  $H_{SF}$  yields the solid line in Fig. 2 which perfectly fits the data in particular around  $H_{SF}$ . The extracted parameters  $M_{DM}^{AF}=2.55 \times 10^{-3} \mu_{\rm B}/{\rm Cu}$  and  $H_{SF}=5.2$  T are in fair agreement with  $2.1 \times 10^{-3} \mu_{\rm B}/{\rm Cu}$  and 5.3 T for a single crystal with  $T_N$  = 240 K, if one takes into account the crystals lower  $T_N$  and the fact that in single crystals  $H_{SF}$  is generally 0.5–1 T larger, most likely because in polycrystals the correlation length is limited by the grain size.<sup>13</sup>

With the developed tools we are now able to track the temperature and doping dependence of  $H_{SF}$ ,  $M_{DM}^{AF}$ , and  $J_{\perp}$  of the five studied samples (Table I). In pure La<sub>2</sub>CuO<sub>4</sub>  $M_{DM}^{AF}$  increases monotonously with decreasing *T*, and extrapolates to  $M_{DM}^{AF}(0)=2.7\times10^{-3} \mu_{\rm B}/{\rm Cu}$  [Fig. 3(a)]. Pure Sr doping causes a drastic reduction of  $M_{DM}^{AF}$ . In contrast, in La<sub>2</sub>CuO<sub>4.85</sub>Zn<sub>0.15</sub>O<sub>4</sub>, though  $T_N$  is strongly reduced, at low



FIG. 3. Spin-flip parameters  $M_{DM}^{AF}$  (a) and  $H_{SF}$  (b)–(e) vs *T* in La<sub>2-x</sub>Sr<sub>x</sub>Cu<sub>1-z</sub>Zn<sub>z</sub>O<sub>4</sub>. Errors in Table I. (b)–(d)  $H_{SF}$  for dH/dt > 0 (upper branches) and dH/dt < 0 (lower branches) as well as mean value (×). (e)  $H_{SF}$  mean values.

temperatures  $M_{DM}^{AF}$  per Cu atom becomes even larger than in La<sub>2</sub>CuO<sub>4</sub>. Quite remarkably, a similar behavior is observed for the Sr/Zn-codoped sample, where the twofold role of Zn is to reduce the mobility of the holes and to create spin vacancies.<sup>6</sup>

In La<sub>2</sub>CuO<sub>4</sub> the spin-flip field  $H_{SF}$  increases with decreasing temperature and below 150 K becomes hysteretic, with its mean value (×) saturating at 4.5 T [Figs. 3(b) and 3(e)]. Pure Sr doping strongly reduces  $H_{SF}$  as well as the hysteretic temperature range. In particular for the 1.7% Sr-doped sample only for  $T \le 10$  K a field hysteresis is observed. Both Zn-doped samples show a relatively large field hysteresis [see Figs. 3(c) and 3(d)]. Their maximum mean value for  $H_{SF}$  is smaller than in La<sub>2</sub>CuO<sub>4</sub>, but in view of their low  $T_N$ , it is large when compared to  $H_{SF}$  of La<sub>1.983</sub>Sr<sub>0.017</sub>CuO<sub>4</sub>. The specific reasons for the hysteresis effects in La<sub>2-x</sub>Sr<sub>x</sub>CuO<sub>4</sub> are not well understood. However, its distinct presence in La<sub>2</sub>CuO<sub>4</sub> indicates that it is not an exclusive feature of the spin freezing regime.

As one can see in Fig. 3(a), in La<sub>2</sub>CuO<sub>4</sub> and for pure Sr doping  $M_{DM}^{AF}$  decreases below 30 K. In the case of La<sub>2</sub>CuO<sub>4</sub> we think that this effect is related to the large field hysteresis of the spin-flip transition, which leads to strongly distorted M(H) curves and makes it difficult to extract reliable  $M_{DM}^{AF}$  values at low temperatures. In contrast, in the 1.7% Sr-doped sample  $M_{DM}^{AF}$  decreases between 30 and 15 K, where M(H) is reversible and the fits of high quality. We think that, here, the effect is connected to the transition into the spin freezing regime and indicates a decrease of the AF order parameter ( $\propto M_{DM}^{AF}$ ), which is consistent with results from neutron diffraction.<sup>7</sup> Obviously, the effect is absent in both Zn-doped samples, which indicates that Zn causes a suppression of the spin freezing regime in La<sub>2-x</sub>Sr<sub>x</sub>CuO<sub>4</sub>.

Following Eq. (1), we show in Fig. 4 the temperature dependence of  $\mathcal{J}_{\perp}^* = M_{DM}^{AF} H_{SF}/S^2$ , which we call the effective interlayer coupling, where  $H_{SF}$  are the mean values in Fig.

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FIG. 4. Interlayer coupling in  $\text{La}_{2-x}\text{Sr}_x\text{Cu}_{1-z}\text{Zn}_z\text{O}_4$ . Errors in Table I. Inset: Inverse correlation length vs *T* for both samples with x=0.017. The solid lines are guides to the eye.

3(e).  $\mathcal{J}_{\perp}^*$  accounts for the effects of doping (x,z) and temperature and only for  $T \rightarrow 0 \mathcal{J}_{\perp}^*(0) = J_{\perp}$ , where  $J_{\perp}$  is the average superexchange per Cu site (Table I), although one should keep in mind that strictly speaking  $J_{\perp}$  is a local interaction. In La<sub>2</sub>CuO<sub>4</sub> we find  $\mathcal{J}^*_{\perp}(0)=2.9 \ \mu eV$ , which is in good agreement with 2.6 µeV for the single crystal mentioned above, if one takes its lower  $T_N$  but relatively high  $H_{\rm SF}$  into account.<sup>13</sup> As a function of Sr doping  $\mathcal{J}_{\perp}^*$  drastically decreases, and for x=0.017  $\mathcal{J}_{\perp}^*(0)$  amounts to only 25% value in  $La_2CuO_4$ . of the In contrast, in  $La_{1.983}Sr_{0.017}Cu_{0.9}Zn_{0.1}O_4$ , which has exactly the same  $T_N$ ,  $\mathcal{J}_{\perp}^*$  increases steeply below  $T_N$  and reaches nearly the same value as in La<sub>2</sub>CuO<sub>4</sub>. La<sub>2</sub>Cu<sub>0.85</sub>Zn<sub>0.15</sub>O<sub>4</sub> behaves similarly. The fact that in both Zn-doped samples  $\mathcal{J}^*_{\perp}(0)$  is about the same as in La<sub>2</sub>CuO<sub>4</sub> reflects Eq. (1), which says that if  $J_{\perp}$  is constant  $H_{SF}$  has to decrease when  $M_{DM}^{AF}$  increases [cf. Figs. 3(a) and 3(e)]. To a certain extent the 15% (z=0.1) and 25% (z=0.15) larger DM moments can be explained by an enhanced octahedra tilt angle  $\Phi$ .<sup>15</sup> Local strain around the non-Jahn-Teller-active Zn sites might amplify this effect. We emphasize that a moderate increase of the DM interaction by Zn doping only will have a small impact on  $J_{\perp}$  and certainly cannot explain the drastic increase by a factor of 4 observed for the two 1.7% Sr-doped samples.

Figure 4 is our major result. It shows that the mechanism for the suppression of the 3D AF order is completely different for pure hole doping (Sr) on the one hand, and nonmagnetic impurity doping (Zn) as well as Sr/Zn codoping on the other hand. In La<sub>2-x</sub>Sr<sub>x</sub>CuO<sub>4</sub> the hole mobility increases rapidly with increasing x, and just a small concentration of mobile holes strongly reduces both  $T_N$  and  $\mathcal{J}_{\perp}^*$ .<sup>6</sup> Codoping with Zn reduces the hole mobility<sup>6</sup> and causes a drastic increase of  $\mathcal{J}_{\perp}^*$  even if  $T_N$  is low. In particular for the two samples with identical  $T_N$  and hole concentration x the effect of different hole mobilities is apparent.

We start the discussion by showing that individual localized holes cannot account for our observations. It is well accepted that localized holes suppress  $T_N$  much stronger than Zn, because holes are located on O sites and ferromagnetically frustrate the antiferromagnetic Cu-O-Cu exchange.<sup>9</sup> In contrast, static spin vacancies do not perturb the AF order of the surrounding Cu spins.<sup>16</sup> To see this we compare the 10% Zn- and 1.7% Sr-codoped sample with localized holes with a  $\sim 18\%$  Zn-doped sample, which would have the same  $T_N$  of ~135 K. It immediately follows that 1.7% localized holes suppress  $T_N$  as effective as 8% Zn. Hence, the in-plane ferromagnetic frustrations of localized holes strongly reduce  $T_N$ , but hardly affect the interlayer coupling (Fig. 4). We conclude that a reduction of the interlayer coupling in La<sub>2-x</sub>Sr<sub>x</sub>CuO<sub>4</sub> is connected to a high hole mobility.

In the following we will show that our observations can be explained assuming dynamic magnetic antiphase boundaries for  $T \ge 30$  K and static for  $T \le 30$  K. Evidence for static antiphase boundaries in the spin freezing regime was recently found by Matsuda et al.7 Below 30 K an incommensurate spin order was detected which coexists with the commensurate AF order. Dynamic antiphase domains were suggested<sup>12</sup> to explain the drastic reduction of the AF order parameter with increasing x for 30 K  $< T < T_N$ . Our discussion does not depend on a particular domain form or on the formation of charge stripes. What is essential is that holes are mobile, as only these holes can ferromagnetically frustrate many Cu-O-Cu-bonds and are able to excite at least antiphase boundary segments. In the presence of many of such excitations a frustration of the interlayer coupling is inevitable, as two antiphased domains in one CuO<sub>2</sub>-plane generally cannot AF couple simultaneously to the adjacent plane.

The drastic reduction of  $M_{DM}^{AF}$  in La<sub>2-x</sub>Sr<sub>x</sub>CuO<sub>4</sub> with increasing x for 30 K  $\leq T < T_N$  can be explained by antiphase boundaries, also. Only those regions of the CuO<sub>2</sub> planes with AF interlayer coupling contribute to the spin flip described by  $M_{SF}$ , while in regions with frustrated interlayer coupling the magnetization of the DM moments contributes to  $M_B$ . In particular for the Sr-doped sample with x=0.017 the significance of  $M_B$  at low T is obvious [Fig. 1(c)]. This clearly

indicates that in  $La_{2-x}Sr_xCuO_4$  with increasing x weight is shifted from  $M_{SF}$  to  $M_B$ , as the regions with AF interlayer coupling, and therefore the AF order parameter, decrease.

According to our analysis, in the 1.7% Sr-doped samples  $\xi_{2D}$  at  $T_N$  is about the same (inset Fig. 4). However, in the sample with mobile holes  $\xi_{2D}$  increases much slower with decreasing T than in the Zn-doped sample with localized holes. Hence, mobile holes seem to confine  $\xi_{2D}$ , which is consistent with the central idea of the finite-size scaling model for the temperature range 30 K  $\leq T < T_N$ .<sup>5,10</sup> However, in this model the spin freezing regime is associated with the breakup of the domain walls when holes localize.<sup>5</sup> In contrast, recent neutron-diffraction data give evidence of static magnetic domain walls in particular in the spin freezing regime.<sup>7</sup>

The additional reduction of  $M_{DM}^{AF}$  in the spin freezing regime can be explained in terms of a static and more even distribution of antiphase boundaries in the spin freezing regime. Since the phase of the AF correlations changes by  $\pi$ on crossing an in-plane antiphase boundary, a periodic arrangement of such domain walls might result in a perfect frustration of the interlayer coupling. The fact that in the Zn-doped samples no drop of  $M_{DM}^{AF}$  below  $T \sim 30$  K is observed, indicates that the localization of holes by Zn destroys the incommensurate spin freezing regime and lifts the frustration of the interlayer coupling. In Ref. 11 it was suggested that Zn effectively removes frustrated in-plane bonds generated by holes. This static picture neglects that it is not favorable for a hole to go on the O site of a Cu-O-Zn bond, for  $Zn^{2+}$  has a full  $3d^{10}$  shell. In contrast, resistivity data suggests that the hole mobility is reduced by impurity scattering.6

In summary, we have presented evidence that the drastic suppression of the antiferromagnetic phase in  $La_{2-x}Sr_xCuO_4$  is associated with a magnetic decoupling of the  $CuO_2$  planes. We concluded that the decoupling is induced by in-plane antiphase boundaries excited by mobile holes. The impact of localized holes as well as static spin vacancies on the interlayer coupling is weak.

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